



#### Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

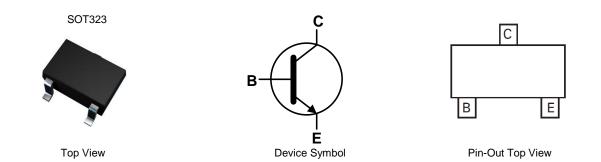
### Features

- BV<sub>CEO</sub> > 80V
- I<sub>C</sub> = 500mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMSTA56Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **80V NPN SMALL SIGNAL TRANSISTOR IN SOT323**

#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



#### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMSTA06Q-7-F	Automotive	K1G	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

Notes:

						SOT323								
								K1G = Product Type Marking Code						
						K1G	₹	YM = Date Code Marking Y or $\overline{Y}$ = Year (ex: D = 2016) M or $\overline{M}$ = Month (ex: 9 = September)						
Date Code	,													
Year	201	6	20	017	2018	2019	2020	2021	2022	2 20	23	2024	2025	2026
Code	D			E	F	G	Н	I	J	ł	<	L	М	Ν
Mont	1 I	Ja	in	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		1		2	3	4	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	4	V
Collector Current	lc	500	mA

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

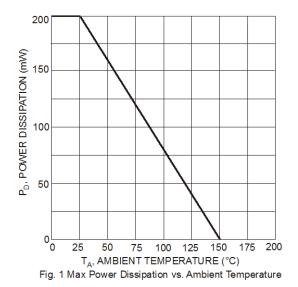
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

# **Thermal Characteristics and Derating Information**





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80		V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	80		V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	4		V	I <sub>E</sub> = 100μA
Collector Base Cutoff Current	I <sub>CBO</sub>	_	100	nA	$V_{CB} = 80V, T_A = +125^{\circ}C$
Collector Cutoff Current	ICES		100	nA	V <sub>CE</sub> = 80V
ON CHARACTERISTICS (Note 8)					·
DC Current Gain	h <sub>FE</sub>	100	_	_	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.25	V	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 10 {\rm mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	1.2	V	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1.0V
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f⊤	100	—	MHz	$V_{CE} = 2.0V, I_C = 10mA,$ f = 100MHz

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



100mA

10

 $T_A = 150^{\circ}C$ 

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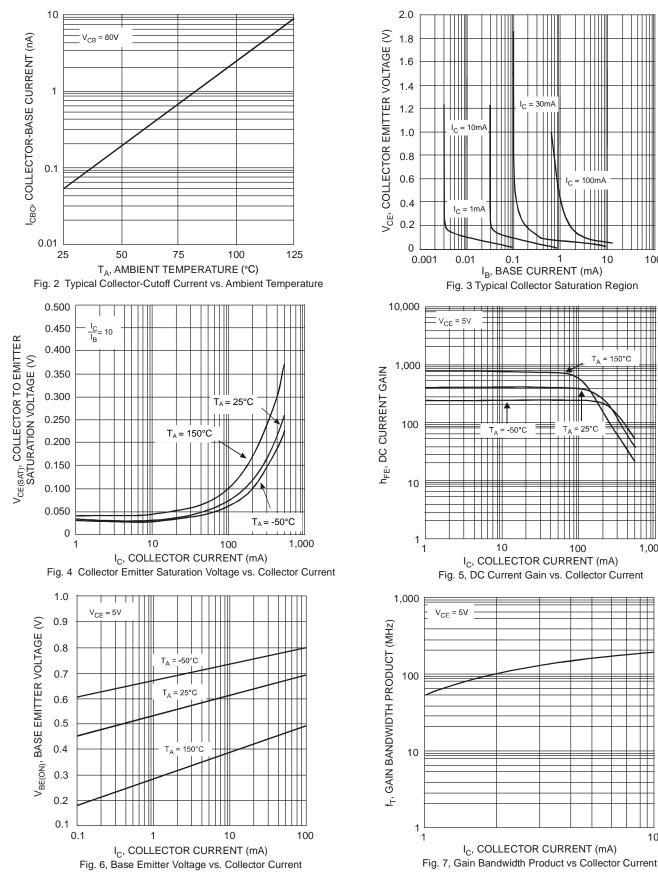
TA = 25°C

100

100

1,000

# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

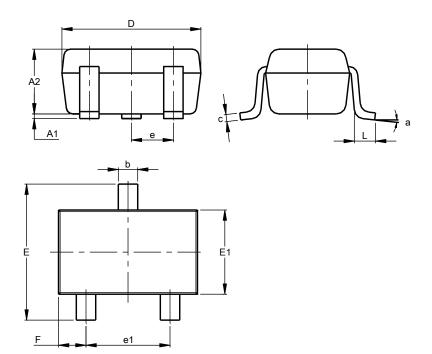


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## **Package Outline Dimensions**

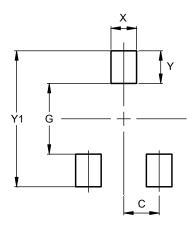
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions	in mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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